# **Complementary Silicon Plastic Power Darlingtons**

 $\ldots$  for use as output devices in complementary general purpose amplifier applications.

- High DC Current Gain
   HFE = 1000 (min.) @ 5 Adc
- Monolithic Construction with Built-in Base Emitter Shunt Resistors

#### **MAXIMUM RATINGS**

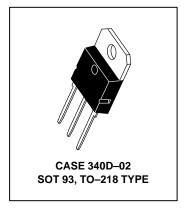
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	100	Vdc
Collector-Base Voltage	V <sub>CB</sub>	100	Vdc
Emitter–Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current — Continuous — Peak	IC	10 20	Adc
Base Current	ΙΒ	0.5	Adc
Total Device Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	PD	125 1.0	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>Stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	1.0	°C/W

# BDV65B PNP BDV64B

DARLINGTONS
10 AMPERES
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60-80-100-120 VOLTS
125 WATTS



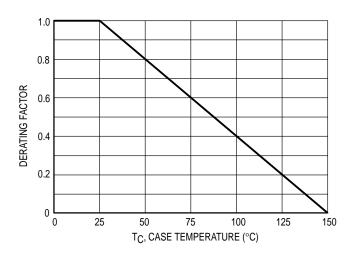


Figure 1. Power Derating

# **BDV65B BDV64B**

# **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0)	VCEO(sus)	100	_	Vdc
Collector Cutoff Current (VCE = 50 Vdc, IB = 0)	I <sub>CEO</sub>	_	1.0	mAdc
Collector Cutoff Current (V <sub>CB</sub> = 100 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	0.4	mAdc
Collector Cutoff Current (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0, T <sub>C</sub> = 150°C)	I <sub>CBO</sub>	_	2.0	mAdc
Emitter Cutoff Current (VBE = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	5.0	mAdc
ON CHARACTERISTICS	<u>.</u>			
DC Current Gain (IC = $5.0$ Adc, $V_{CE} = 4.0$ Vdc)	hFE	1000	_	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 5.0 Adc, I <sub>B</sub> = 0.02 Adc)	VCE(sat)	_	2.0	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	VBE(on)	_	2.5	Vdc

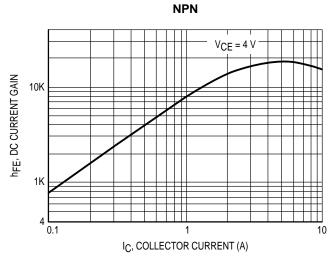


Figure 2. DC Current Gain

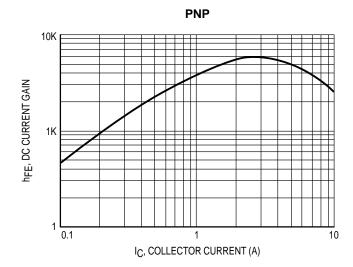


Figure 3. DC Current Gain

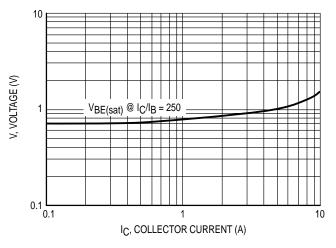


Figure 4. "On" Voltages

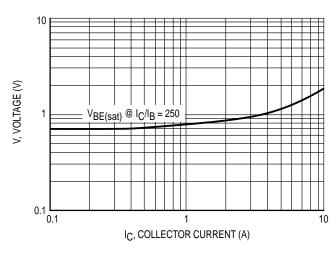


Figure 5. "On" Voltages

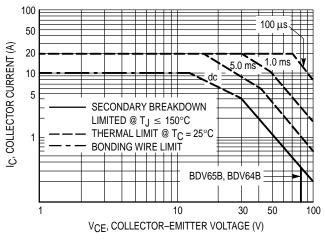


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^{\circ}C$ ,  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 7. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

## **BDV65B BDV64B**

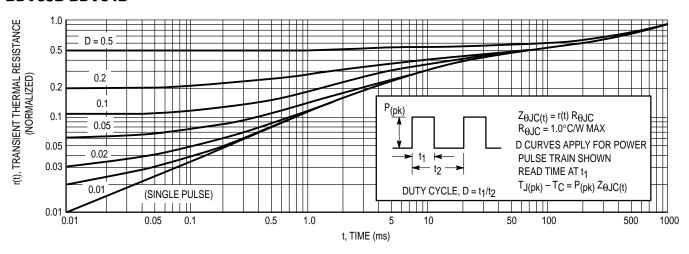
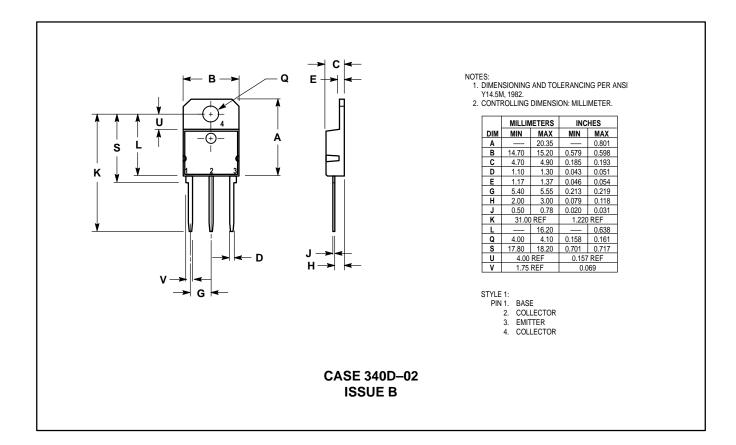


Figure 7. Thermal Response

## **PACKAGE DIMENSIONS**



#### **BDV65B BDV64B**

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